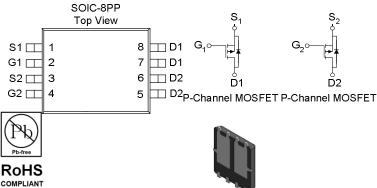
## Dual P-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, communication equipments.

•	Low $r_{DS(on)}$ provides higher efficiency and
	extends battery life

- Low thermal impedance copper leadframe SOIC-8PP saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)} m(\Omega)$	$I_{D}(A)$		
-30	$13 @ V_{GS} = 10V$	29		
-30	$18 @ V_{GS} = 4.5V$	25		



ABSOLUTE MAXIMUM RATINGS ( $T_A = 25$ °C UNLESS OTHERWISE NO					
Parameter	Symbol	Units			
Drain-Source Voltage	$V_{DS}$	-30	V		
Gate-Source Voltage			20	v	
	$T_A=25^{\circ}C$	т	29		
Continuous Drain Current <sup>a</sup>	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	$\mathbf{I}_{\mathrm{D}}$	24	A	
Pulsed Drain Current <sup>b</sup>	$I_{DM}$	±50			
Continuous Source Current (Diode Conduct	$I_S$	13	A		
D a	$T_A=25^{\circ}C$	D	16	W	
Power Dissipation <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	$P_{\mathrm{D}}$	10	VV	
Operating Junction and Storage Temperatur	$T_J, T_{stg}$	-55 to 150	°C		

HALOGEN FREE

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Maximum	Units		
M · T · · · a	t <= 10 sec	$R_{ heta JA}$	35	0CMV	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	$R_{ heta JC}$	8	°C/W	

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## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Analog Power AM7931P

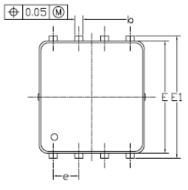
Donomoton	Cymbal	Test Conditions	Limits			T I 24	
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static	-					-	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-1				
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±10	μΑ	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	Δ	
Zero Gate Voltage Drain Current	1 <sub>DSS</sub>	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-10	μΑ	
On-State Drain Current <sup>A</sup>	$I_{D(on)}$	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-20			A	
Drain-Source On-Resistance <sup>A</sup>		$V_{GS} = -10 \text{ V}, I_{D} = -1 \text{ A}$			13	mΩ	
Drain-Source On-Resistance	r <sub>DS(on)</sub>	$V_{GS} = -4.5 \text{ V}, I_{D} = -1 \text{ A}$			18		
Forward Tranconductance <sup>A</sup>	${f g}_{ m fs}$	$V_{DS} = -15 \text{ V}, I_{D} = -1 \text{ A}$		8		S	
Diode Forward Voltage	$V_{\mathrm{SD}}$	$I_S = -1 A$ , $V_{GS} = 0 V$		-0.7		V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_{g}$	$V_{DS} = -30 \text{ V}, V_{GS} = -4.5 \text{ V},$		25			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = -30 \text{ V}, V_{GS} = -4.5 \text{ V},$ $I_{D} = -1 \text{ A}$		7		nC	
Gate-Drain Charge	$Q_{\mathrm{gd}}$	I <sub>D</sub> – -1 A		10		]	
Turn-On Delay Time	t <sub>d(on)</sub>			14			
Rise Time	t <sub>r</sub>	$V_{DD} = -30 \text{ V},  R_L = 30 \; \Omega \;$ , ID = -1 A,		5		nS	
Turn-Off Delay Time	$t_{d(off)}$	$VGEN = -10 \text{ V},  RG = 6\Omega$		86		113	
Fall-Time	$t_{\mathrm{f}}$			15			

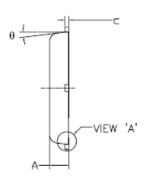
## Notes

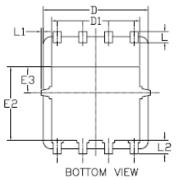
- a. Pulse test:  $PW \le 300$ us duty cycle  $\le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

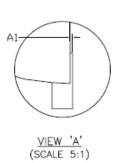
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## Package Information









SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
SIMBOLS	MIN	NOM	MAX	MIN	NOM	MAX	
A	0.85	0.95	1.00	0.033	0.037	0.039	
A1	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
С	0.15	0. 20	0. 25	0.006	0.008	0.010	
D	5. 20 BSC			0. 205 BSC			
D1	4.35 BSC			0.171 BSC			
E	5. 55 BSC			0. 219 BSC			
E1	6. 05 BSC			0. 238 BSC			
E2	3. 625 BSC			0.143 BSC			
E3	1. 275 BSC			0.050 BSC			
e	1. 27 BSC			0.050 BSC			
L	0.45	0. 55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	